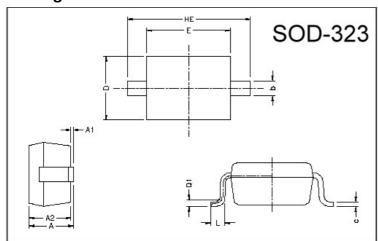
## GDBAS16

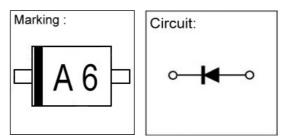
# SURFACE MOUNT, SWITCHING DIODE VOLTAGE 85V, CURRENT 250mA

#### **Description**

The GDBAS16 is designed for high-speed switching application in hybrid thick and thin-film circuits. The devices is manufactured by the silicon epitaxial planar process and packed in a plastic surface mount package.

#### **Package Dimensions**





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.	nLI.	Min.	Max.
Α	0.85	1.05			
A1	0	0.10	L	0.20	0.40
A2	0.80	1.00	b	0.25	0.40
D	1.15	1.45	С	0.10	0.18
Е	1.60	1.80			
HE	2.30	2.70	Q1	0.15 BSC.	

### Absolute Maximum Ratings at TA = $25^{\circ}$ C

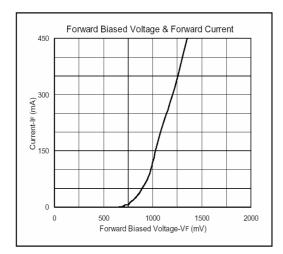
Tj Teta	+150	°C
Teta		
1319	-65 ~ +150	$^{\circ}\mathbb{C}$
VR	85	V
VRRM	85	V
lo	250	mA
IFM	500	mA
IFSM	1000	mA
PD	225	mW
	VRRM IO IFM IFSM	VR 85 VRRM 85 IO 250 IFM 500 IFSM 1000

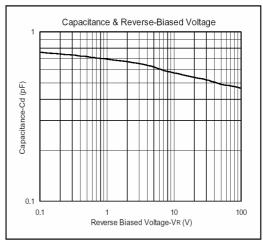
### **Electrical Characteristics** (at TA = 25°C unless otherwise noted)

Characteristic	Symbol	Min.	Max.	Unit	Test Conditions
Reverse Breakdown Voltage	V(BR)	85	-	V	IR=100uA
	VF(1)	-	715	mV	IF=1mA
Forward Voltogo	VF(2)	-	855	mV	IF=10mA
Forward Voltage	VF(3)	-	1000	mV	IF=50mA
	VF(4)	-	1250	mV	IF=150mA
Reverse Current	IR	-	1	uA	V <sub>R</sub> =85V
Total Capacitance	Ст		2	pF	V <sub>R</sub> =0, f=1MHz
Reverse Recovery Time	Trr	-	6	nS	I <sub>F</sub> =I <sub>R</sub> =10mA, R <sub>L</sub> =100Ω measured at I <sub>R</sub> =1mA

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#### **Characteristics Curve**





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